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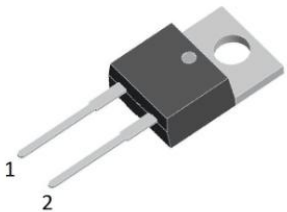
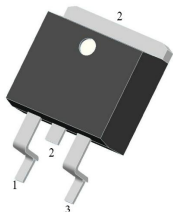
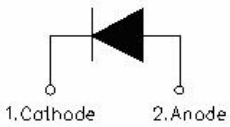
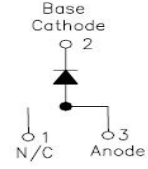
## MBR1060/MBRB1060 SCHOTTKY RECTIFIER

### Features

- 150°C T<sub>J</sub> operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Applications

- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection

<p style="text-align: center;">MBR1060</p> 	<p style="text-align: center;">MBRB1060</p> 
 <p style="text-align: center;">1.Cathode    2.Anode</p>	 <p style="text-align: center;">Base Cathode 2 1 N/C    3 Anode</p>
<p style="text-align: center;">TO-220AC</p>	<p style="text-align: center;">D<sup>2</sup>PAK</p>

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	60	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>c</sub> =100°C, rectangular wave form	10	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	150	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@10A, Pulse, T <sub>J</sub> = 25 °C	0.65	0.80	V
	V <sub>F2</sub>	@10A, Pulse, T <sub>J</sub> = 125 °C	0.60	0.70	V
Reverse Current *	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.008	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 °C	3	6	mA
Max. Junction Capacitance	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	280	400	pF
Series Inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

\* Pulse width < 300 μs, duty cycle < 2%

### Thermal-Mechanical Specifications:

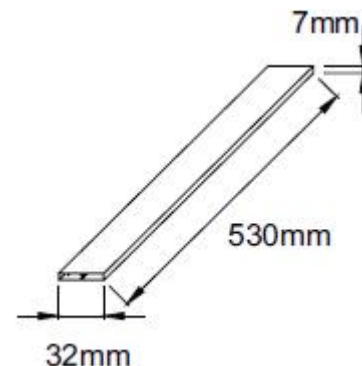
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	DC operation	2.0	°C/W
Typical Thermal Resistance, Case to Heat Sink	R <sub>θJS</sub>	DC operation	0.5	°C/W
Case Style	TO-220AC D <sup>2</sup> PAK			

### Tube Specification

Device	Package	Weight	Shipping
MBR1060	TO-220AC	1.8g	50pcs / tube
MBRB1060	D <sup>2</sup> PAK	1.85g	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### Tube Specification(TO-220AC)





## Ratings and Characteristics Curves

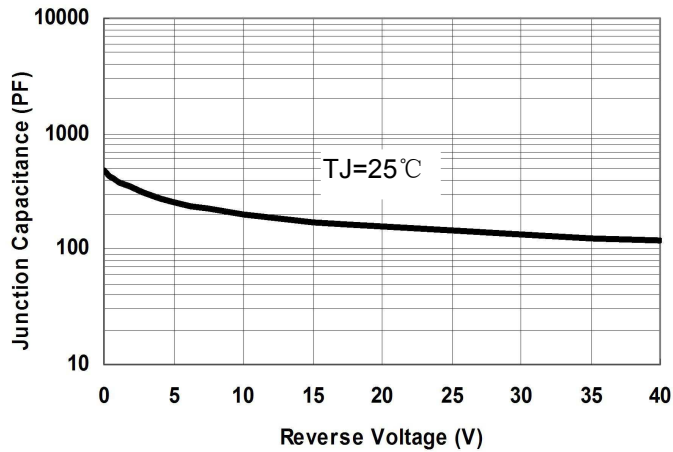


Fig.1-Typical Junction Capacitance

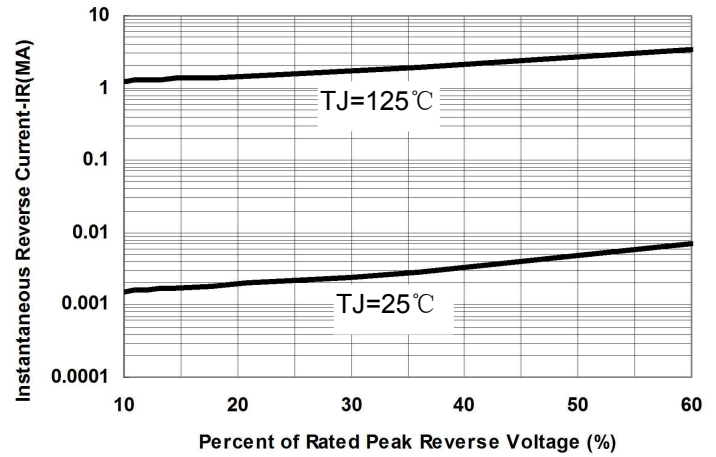


Fig.2-Typical Reverse Characteristics

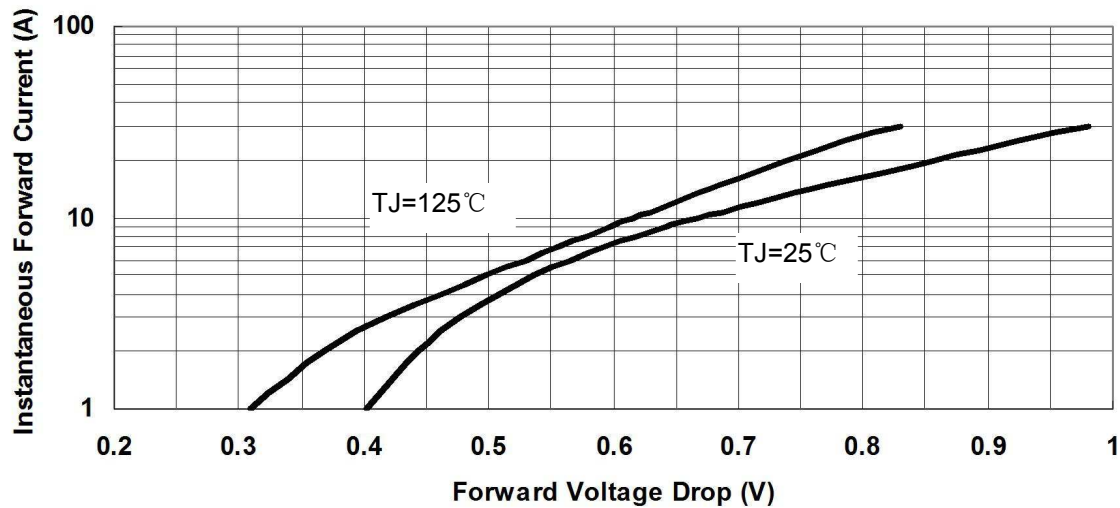
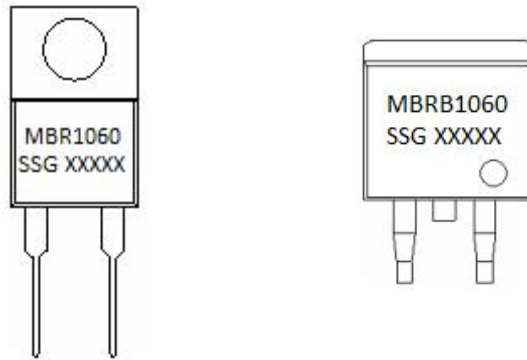


Fig.3-Typical Instantaneous Forward Voltage Characteristics

## Marking Diagram

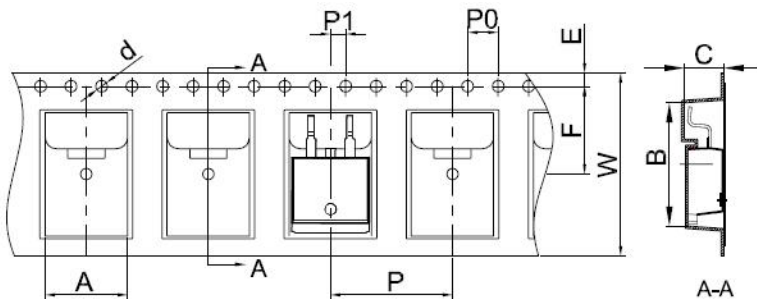


Where XXXXX is YYWWL

MBR = Device Type  
B = Package type  
10 = Forward Current (10A)  
60 = Reverse Voltage (60V)  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

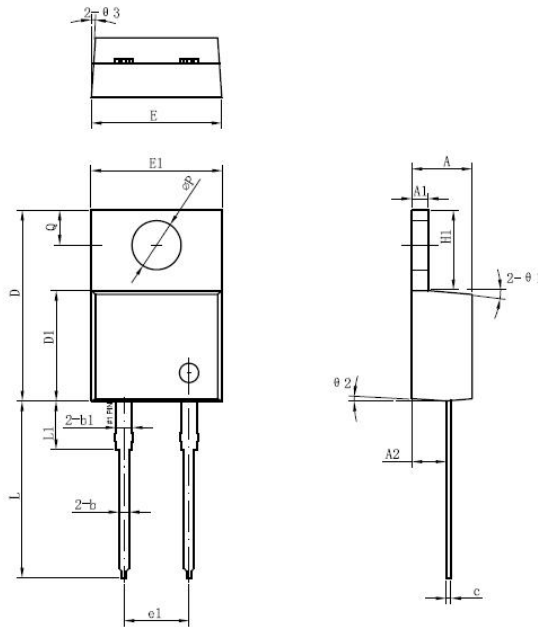
**Cautions:** Molding resin  
Epoxy resin UL:94V-0

## Carrier Tape Specification D<sup>2</sup>PAK



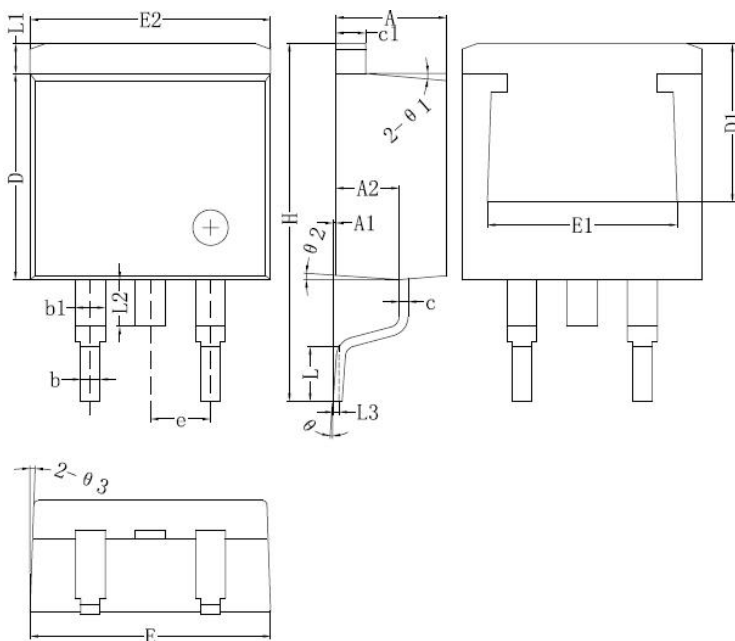
Symbol	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

**Mechanical Dimensions TO-220AC**



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	1.17	1.27	1.37
A2	2.52	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
D	14.64	14.94	15.24
D1	8.50	8.07	8.90
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1	4.98	5.08	5.18
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1	3.56	3.80	3.96
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	

**Mechanical Dimensions D<sup>2</sup>PAK**



Symbol	Millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

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